Vladimir Dubrovskii

List of Publications by Year in Descending Order

274 papers	5,745 citations	43 h-index	66 g-index
300 ext. papers	6,308 ext. citations	3 avg, IF	6.3 L-index

#	Paper	IF	Citations
274	Theory of MBE Growth of Nanowires on Reflecting Substrates.. *Nanomaterials*, **2022**, 12,	5.4	3
273	Theory of MBE Growth of Nanowires on Adsorbing Substrates: The Role of the Shadowing Effect on the Diffusion Transport.. *Nanomaterials*, **2022**, 12,	5.4	1
272	Modeling the Radial Growth of Self-Catalyzed III-V Nanowires. *Nanomaterials*, **2022**, 12, 1698	5.4	0
271	In Situ Monitoring of MBE Growth of a Single Self-Catalyzed GaAs Nanowire by X-ray Diffraction. *Journal of Physical Chemistry C*, **2021**, 125, 22724-22732	3.8	3
270	Vapor□Liquid□Solid Growth of Semiconductor Nanowires **2021**, 3-107		5
269	Simultaneous Selective Area Growth of Wurtzite and Zincblende Self-Catalyzed GaAs Nanowires on Silicon. *Nano Letters*, **2021**, 21, 3139-3145	11.5	7
268	Modeling the Shape Evolution of Selective Area Grown Zn3P2 Nanoislands. *Crystal Growth and Design*, **2021**, 21, 4732-4737	3.5	0
267	Formation of Hexagonal Ge Stripes on the Side Facets of AlGaAs Nanowires: Implications for Near-Infrared Detectors. *ACS Applied Nano Materials*, **2021**, 4, 7289-7294	5.6	1
266	Long catalyst-free InAs nanowires grown on silicon by HVPE. *CrystEngComm*, **2021**, 23, 378-384	3.3	3
265	Conformal Growth of Radial InGaAs Quantum Wells in GaAs Nanowires. *Journal of Physical Chemistry Letters*, **2021**, 12, 1275-1283	6.4	4
264	Reconsideration of Nanowire Growth Theory at Low Temperatures. *Nanomaterials*, **2021**, 11,	5.4	2
263	Formation of wurtzite sections in self-catalyzed GaP nanowires by droplet consumption. *Nanotechnology*, **2021**, 32,	3.4	2
262	Comprehensive model toward optimization of SAG In-rich InGaN nanorods by hydride vapor phase epitaxy. *Nanotechnology*, **2021**, 32, 155601	3.4	
261	Kinetic broadening of size distribution in terms of natural versus invariant variables. *Physical Review E*, **2021**, 103, 012112	2.4	
260	Gallium Diffusion Flow Direction during Deposition on the Surface with Regular Hole Arrays. *Technical Physics Letters*, **2021**, 47, 601-604	0.7	0
259	Nanoisland Shape Variation during Selective Epitaxy. *Technical Physics Letters*, **2021**, 47, 701-704	0.7	
258	The Dependence of the Growth Rate and Structure of III□V Nanowires on the Adatom Collection Area on the Substrate Surface. *Technical Physics Letters*, **2021**, 47, 440-443	0.7	

257	Oscillations of As Concentration and Electron-to-Hole Ratio in Si-Doped GaAs Nanowires. *Nanomaterials*, **2020**, 10,	5.4	2
256	Dynamics of Gold Droplet Formation on SiO2/Si(111) Surface. *Journal of Physical Chemistry C*, **2020**, 124, 11946-11951	3.8	7
255	Effect of Arsenic Depletion on the Silicon Doping of Vapor□iquid□olid GaAs Nanowires. *Physica Status Solidi - Rapid Research Letters*, **2020**, 14, 2000129	2.5	3
254	Impact of droplet composition on the nucleation rate and morphology of vapor-liquid-solid GeSn nanowires. *Nanotechnology*, **2020**, 31, 405602	3.4	2
253	MBE-Grown InxGa1 □As Nanowires with 50% Composition. *Semiconductors*, **2020**, 54, 650-653	0.7	1
252	Surface Diffusion of Gallium as the Origin of Inhomogeneity in Selective Area Growth of GaN Nanowires on AlxOy Nucleation Stripes. *Crystal Growth and Design*, **2020**, 20, 4770-4778	3.5	4
251	Formation of voids in selective area growth of InN nanorods in SiNx on GaN templates. *Nano Futures*, **2020**, 4, 025002	3.6	4
250	Growth of Self-Catalyzed InAs/InSb Axial Heterostructured Nanowires: Experiment and Theory. *Nanomaterials*, **2020**, 10,	5.4	1
249	Kinetics of Nucleus Growth from a Nanophase. *Technical Physics Letters*, **2020**, 46, 357-360	0.7	1
248	Phase Selection in Self-catalyzed GaAs Nanowires. *Nano Letters*, **2020**, 20, 1669-1675	11.5	49
247	Formation Mechanism of Twinning Superlattices in Doped GaAs Nanowires. *Nano Letters*, **2020**, 20, 3344-3351	11.5	9
246	Energetics and kinetics of monolayer formation in vapor-liquid-solid nanowire growth. *Physical Review Materials*, **2020**, 4,	3.2	3
245	Modeling the dynamics of interface morphology and crystal phase change in self-catalyzed GaAs nanowires. *Nanotechnology*, **2020**, 31, 485602	3.4	2
244	GaAs nanoscale membranes: prospects for seamless integration of III-Vs on silicon. *Nanoscale*, **2020**, 12, 815-824	7.7	9
243	Kinetics and mechanism of planar nanowire growth. *Proceedings of the National Academy of Sciences of the United States of America*, **2020**, 117, 152-160	11.5	10
242	Selective Area Growth of GaN Nanowires on Graphene Nanodots. *Crystal Growth and Design*, **2020**, 20, 552-559	3.5	11
241	Limits of III□ Nanowire Growth. *Technical Physics Letters*, **2020**, 46, 859-863	0.7	1
240	Free Energy of Nucleus Formation during Growth of III□ Semiconductor Nanowires. *Technical Physics Letters*, **2020**, 46, 889-892	0.7	

239	Be, Te, and Si Doping of GaAs Nanowires: Theory and Experiment. *Journal of Physical Chemistry C*, **2020**, 124, 17299-17307	3.8	6
238	Ga2Se3 Nanowires via Au-Assisted Heterovalent Exchange Reaction on GaAs. *Journal of Physical Chemistry C*, **2020**, 124, 17783-17794	3.8	0
237	Growth Kinetics of Planar Nanowires. *Technical Physics Letters*, **2020**, 46, 1008-1011	0.7	
236	InAs/InP core/shell nanowire gas sensor: Effects of InP shell on sensitivity and long-term stability. *Applied Surface Science*, **2019**, 498, 143756	6.7	4
235	Quasi One-Dimensional Metal-Semiconductor Heterostructures. *Nano Letters*, **2019**, 19, 3892-3897	11.5	4
234	Si Doping of Vapor-Liquid-Solid GaAs Nanowires: n-Type or p-Type?. *Nano Letters*, **2019**, 19, 4498-4504	11.5	17
233	Evolution of the Length and Radius of Catalyst-Free III-V Nanowires Grown by Selective Area Epitaxy. *ACS Omega*, **2019**, 4, 8400-8405	3.9	6
232	Modeling selective-area growth of InAsSb nanowires. *Nanotechnology*, **2019**, 30, 285601	3.4	7
231	Contact angle stability of gold droplets on top of GaAs nanowires in the non-stationary case. *Journal of Physics: Conference Series*, **2019**, 1199, 012024	0.3	
230	Does desorption affect the length distributions of nanowires?. *Nanotechnology*, **2019**, 30, 475604	3.4	2
229	Photovoltaic Light Funnels Grown by GaAs Nanowire Droplet Dynamics. *IEEE Journal of Photovoltaics*, **2019**, 9, 1225-1231	3.7	2
228	Nucleation-limited composition of Al1-xInxAs nanowires. *Journal of Physics: Conference Series*, **2019**, 1199, 012022	0.3	
227	Classification of the Morphologies and Related Crystal Phases of IIIV Nanowires Based on the Surface Energy Analysis. *Journal of Physical Chemistry C*, **2019**, 123, 18693-18701	3.8	7
226	Stabilization of the Morphology and Crystal Phase in Ensembles of Self-Catalyzed GaAs Nanowires. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900301	2.5	4
225	Analysis of incubation time preceding the Ga-assisted nucleation and growth of GaAs nanowires on Si(111). *Physical Review Materials*, **2019**, 3,	3.2	3
224	Te incorporation and activation as n-type dopant in self-catalyzed GaAs nanowires. *Physical Review Materials*, **2019**, 3,	3.2	12
223	Fundamental aspects to localize self-catalyzed III-V nanowires on silicon. *Nature Communications*, **2019**, 10, 869	17.4	33
222	Effect of Elastic Stresses on the Formation of Axial Heterojunctions in Ternary AIIIBV Nanowires. *Physics of the Solid State*, **2019**, 61, 2459-2463	0.8	2

221	Analytic form of the size distribution in irreversible growth of nanoparticles. *Physical Review E*, **2019**, 99, 012105	2.4	5
220	Compositional control of homogeneous InGaN nanowires with the In content up to 90. *Nanotechnology*, **2019**, 30, 044001	3.4	6
219	Deterministic Switching of the Growth Direction of Self-Catalyzed GaAs Nanowires. *Nano Letters*, **2019**, 19, 82-89	11.5	11
218	Nucleation-limited composition of ternary III□V nanowires forming from quaternary gold based liquid alloys. *CrystEngComm*, **2018**, 20, 1649-1655	3.3	21
217	Tuning the morphology of self-assisted GaP nanowires. *Nanotechnology*, **2018**, 29, 225603	3.4	14
216	Bistability of Contact Angle and Its Role in Achieving Quantum-Thin Self-Assisted GaAs nanowires. *Nano Letters*, **2018**, 18, 49-57	11.5	46
215	Template-Assisted Scalable Nanowire Networks. *Nano Letters*, **2018**, 18, 2666-2671	11.5	61
214	Influence of Silicon on the Nucleation Rate of GaAs Nanowires on Silicon Substrates. *Journal of Physical Chemistry C*, **2018**, 122, 19230-19235	3.8	11
213	Nanoparticle Stability in Axial InAs-InP Nanowire Heterostructures with Atomically Sharp Interfaces. *Nano Letters*, **2018**, 18, 167-174	11.5	16
212	Nucleation and Growth Modeling of Protein Crystals in Capillaries. *Semiconductors*, **2018**, 52, 2132-2134	0.7	
211	Suppression of miscibility gaps in vapor-liquid-solid InGaAs and InGaN nanowires. *Journal of Physics: Conference Series*, **2018**, 1124, 022031	0.3	1
210	Theoretical analysis of the length distributions of Ga-catalyzed GaAs nanowires. *Journal of Physics: Conference Series*, **2018**, 1124, 022039	0.3	
209	A simple route to synchronized nucleation of self-catalyzed GaAs nanowires on silicon for sub-Poissonian length distributions. *Nanotechnology*, **2018**, 29, 504004	3.4	14
208	Circumventing the miscibility gap in InGaN nanowires emitting from blue to red. *Nanotechnology*, **2018**, 29, 465602	3.4	13
207	Optimizing the yield of A-polar GaAs nanowires to achieve defect-free zinc blende structure and enhanced optical functionality. *Nanoscale*, **2018**, 10, 17080-17091	7.7	22
206	Compositional control of gold-catalyzed ternary nanowires and axial nanowire heterostructures based on III□P1□Asx. *Journal of Crystal Growth*, **2018**, 498, 179-185	1.6	4
205	Model for large-area monolayer coverage of polystyrene nanospheres by spin coating. *Scientific Reports*, **2017**, 7, 40888	4.9	22
204	Scaling of size distributions of C60 and C70 fullerene surface islands. *Applied Surface Science*, **2017**, 407, 117-120	6.7	1

203	Length distributions of nanowires: Effects of surface diffusion versus nucleation delay. *Journal of Crystal Growth*, **2017**, 463, 139-144	1.6	10
202	Exactly solvable model for cluster-size distribution in a closed system. *Physical Review E*, **2017**, 95, 012135	2.4	2
201	Self-catalyzed GaAs nanowires on silicon by hydride vapor phase epitaxy. *Nanotechnology*, **2017**, 28, 125602	3.4	11
200	Refinement of Nucleation Theory for Vapor–Liquid–Solid Nanowires. *Crystal Growth and Design*, **2017**, 17, 2589-2593	3.5	24
199	Engineering the Size Distributions of Ordered GaAs Nanowires on Silicon. *Nano Letters*, **2017**, 17, 4101-4108	11.5	34
198	CdTe Nanowires by Au-Catalyzed Metalorganic Vapor Phase Epitaxy. *Nano Letters*, **2017**, 17, 4075-4082	11.5	11
197	Development of Growth Theory for Vapor–Liquid–Solid Nanowires: Contact Angle, Truncated Facets, and Crystal Phase. *Crystal Growth and Design*, **2017**, 17, 2544-2548	3.5	37
196	A simplified model to estimate thermal resistance between carbon nanotube and sample in scanning thermal microscopy. *Journal Physics D: Applied Physics*, **2017**, 50, 494004	3	8
195	Understanding the vapor–liquid–solid growth and composition of ternary III–V nanowires and nanowire heterostructures. *Journal Physics D: Applied Physics*, **2017**, 50, 453001	3	14
194	Three-fold Symmetric Doping Mechanism in GaAs Nanowires. *Nano Letters*, **2017**, 17, 5875-5882	11.5	22
193	Sub-Poissonian Narrowing of Length Distributions Realized in Ga-Catalyzed GaAs Nanowires. *Nano Letters*, **2017**, 17, 5350-5355	11.5	31
192	Inhomogeneous dopant distribution in III–V nanowires. *Semiconductors*, **2017**, 51, 1427-1430	0.7	
191	Understanding the composition of ternary III-V nanowires and axial nanowire heterostructures in nucleation-limited regime. *Materials and Design*, **2017**, 132, 400-408	8.1	27
190	Dispersion of scale-invariant size-distribution functions. *Technical Physics Letters*, **2017**, 43, 413-415	0.7	
189	Doping profiles during nanowire growth via the vapor-liquid-solid mechanism. *Journal of Physics: Conference Series*, **2017**, 917, 032025	0.3	
188	Length distributions of Au-catalyzed III-V nanowires in different regimes of the diffusion-induced growth. *Journal of Physics: Conference Series*, **2017**, 917, 032043	0.3	
187	Self-narrowing of size distributions of nanostructures by nucleation antibunching. *Physical Review Materials*, **2017**, 1,	3.2	18
186	Sub-Poissonian length distributions of vapor–liquid–solid nanowires induced by nucleation antibunching. *Journal Physics D: Applied Physics*, **2017**, 50, 254004	3	2

185	Spontaneous formation of GaN/AlN core–shell nanowires on sapphire by hydride vapor phase epitaxy. *Journal of Crystal Growth*, **2016**, 454, 1-5	1.6	3
184	The length distribution function of semiconductor filamentary nanocrystals. *Technical Physics Letters*, **2016**, 42, 682-685	0.7	1
183	The initial stage of autocatalytic growth of GaAs filamentary nanocrystals. *Technical Physics Letters*, **2016**, 42, 818-821	0.7	
182	Length distributions of Au-catalyzed and In-catalyzed InAs nanowires. *Nanotechnology*, **2016**, 27, 375602	3.4	27
181	Kinetic narrowing of size distribution. *Physical Review B*, **2016**, 93,	3.3	5
180	Origin of Spontaneous Core–Shell AlGaAs Nanowires Grown by Molecular Beam Epitaxy. *Crystal Growth and Design*, **2016**, 16, 7251-7255	3.5	27
179	Analysis of Incubation Times for the Self-Induced Formation of GaN Nanowires: Influence of the Substrate on the Nucleation Mechanism. *Crystal Growth and Design*, **2016**, 16, 7205-7211	3.5	19
178	Molecular beam epitaxy of InAs nanowires in SiO nanotube templates: challenges and prospects for integration of III-Vs on Si. *Nanotechnology*, **2016**, 27, 455601	3.4	7
177	Catalyst Composition Tuning: The Key for the Growth of Straight Axial Nanowire Heterostructures with Group III Interchange. *Nano Letters*, **2016**, 16, 7183-7190	11.5	22
176	Simultaneous Selective-Area and Vapor-Liquid-Solid Growth of InP Nanowire Arrays. *Nano Letters*, **2016**, 16, 4361-7	11.5	46
175	Regimes of radial growth for Ga-catalyzed GaAs nanowires. *Applied Physics A: Materials Science and Processing*, **2016**, 122, 1	2.6	4
174	Scanning thermal microscopy with heat conductive nanowire probes. *Ultramicroscopy*, **2016**, 162, 42-51	3.1	20
173	Factors Influencing the Interfacial Abruptness in Axial III–V Nanowire Heterostructures. *Crystal Growth and Design*, **2016**, 16, 2019-2023	3.5	18
172	Group V sensitive vapor–liquid–solid growth of Au-catalyzed and self-catalyzed III–V nanowires. *Journal of Crystal Growth*, **2016**, 440, 62-68	1.6	27
171	Self-equilibration of the radius distribution in self-catalyzed GaAs nanowires. *Journal of Physics: Conference Series*, **2016**, 741, 012033	0.3	
170	Contribution of droplet volume fluctuation to dispersion of nanowire length. *Journal of Physics: Conference Series*, **2016**, 741, 012040	0.3	
169	On a new method of heterojunction formation in III–V nanowires. *Semiconductors*, **2016**, 50, 1566-1568	0.7	
168	Incubation time of heterogeneous growth of islands in the mode of incomplete condensation. *Technical Physics Letters*, **2016**, 42, 1103-1106	0.7	2

167	Self-induced GaN nanowire growth: surface density determination. *Journal of Physics: Conference Series*, **2016**, 741, 012032	0.3	
166	Chemical potentials and growth rates of gold-catalyzed ternary InGaAs nanowires. *Journal of Physics: Conference Series*, **2016**, 741, 012010	0.3	
165	Broadening of length distributions of Au-catalyzed InAs nanowires **2016**,		1
164	Length Distributions of Nanowires Growing by Surface Diffusion. *Crystal Growth and Design*, **2016**, 16, 2167-2172	3.5	33
163	A model of axial heterostructure formation in III–V semiconductor nanowires. *Technical Physics Letters*, **2016**, 42, 332-335	0.7	2
162	Quaternary Chemical Potentials for Gold-Catalyzed Growth of Ternary InGaAs Nanowires. *Crystal Growth and Design*, **2016**, 16, 4526-4530	3.5	15
161	Gallium nitride nanowires and microwires with exceptional length grown by metal organic chemical vapor deposition via titanium film. *Journal of Applied Physics*, **2015**, 117, 024301	2.5	7
160	Control of morphology and crystal purity of InP nanowires by variation of phosphine flux during selective area MOMBE. *Nanotechnology*, **2015**, 26, 085303	3.4	27
159	Tailoring the diameter and density of self-catalyzed GaAs nanowires on silicon. *Nanotechnology*, **2015**, 26, 105603	3.4	53
158	Scale invariance of continuum size distribution upon irreversible growth of surface islands. *Technical Physics Letters*, **2015**, 41, 526-528	0.7	1
157	Analytic scaling function for island-size distributions. *Physical Review E*, **2015**, 91, 042408	2.4	14
156	Self-Equilibration of the Diameter of Ga-Catalyzed GaAs Nanowires. *Nano Letters*, **2015**, 15, 5580-4	11.5	90
155	The theory of nucleation and polytypism of III–V semiconductor nanowires. *Technical Physics Letters* , **2015**, 41, 203-207	0.7	4
154	Scaling size distribution functions of heterogeneous clusters in a linear capture coefficient model. *Technical Physics Letters*, **2015**, 41, 242-245	0.7	2
153	Mono- and polynucleation, atomistic growth, and crystal phase of III-V nanowires under varying group V flow. *Journal of Chemical Physics*, **2015**, 142, 204702	3.9	20
152	Understanding the growth and composition evolution of gold-seeded ternary InGaAs nanowires. *Nanoscale*, **2015**, 7, 16266-72	7.7	30
151	Fully Analytical Description for the Composition of Ternary Vapor–Liquid–Solid Nanowires. *Crystal Growth and Design*, **2015**, 15, 5738-5743	3.5	26
150	Zeldovich Nucleation Rate, Self-Consistency Renormalization, and Crystal Phase of Au-Catalyzed GaAs Nanowires. *Crystal Growth and Design*, **2015**, 15, 340-347	3.5	48

149	Framed carbon nanostructures: synthesis and applications in functional SPM tips. *Ultramicroscopy*, **2015**, 148, 151-157	3.1	18
148	Self-consistent renormalization in the theory of binary nucleation in ternary solutions. *Technical Physics Letters*, **2015**, 41, 915-918	0.7	
147	Natural scaling of size distributions in homogeneous and heterogeneous rate equations with size-linear capture rates. *Journal of Chemical Physics*, **2015**, 142, 124110	3.9	5
146	Modelling polytypism in III-V nanowires: role of group V and nucleation patterns during the growth. *Journal of Physics: Conference Series*, **2015**, 643, 012017	0.3	
145	Self-limiting growth and bimodal size distribution of Au nanoislands on InAs(111)B surface. *Journal of Physics: Conference Series*, **2015**, 643, 012012	0.3	1
144	Conditions for high yield of selective-area epitaxy InAs nanowires on SiO x /Si(111) substrates. *Nanotechnology*, **2015**, 26, 465301	3.4	20
143	Model of selective growth of III□V nanowires. *Technical Physics Letters*, **2015**, 41, 1136-1138	0.7	
142	Catalyst-free growth of InAs nanowires on Si (111) by CBE. *Nanotechnology*, **2015**, 26, 415604	3.4	25
141	Determination of the diffusion lengths of Ga adatoms using GaN stripe profiling. *Physica Status Solidi (A) Applications and Materials Science*, **2015**, 212, 851-854	1.6	15
140	Theory of VLS Growth of Compound Semiconductors. *Semiconductors and Semimetals*, **2015**, 93, 1-78	0.6	22
139	Size distributions of fullerene surface clusters. *Applied Surface Science*, **2014**, 307, 46-51	6.7	12
138	Influence of the group V element on the chemical potential and crystal structure of Au-catalyzed III-V nanowires. *Applied Physics Letters*, **2014**, 104, 053110	3.4	66
137	Modeling the nucleation statistics in vapor□liquid□solid nanowires. *Journal of Crystal Growth*, **2014**, 401, 51-55	1.6	12
136	Nucleation Theory and Growth of Nanostructures. *Nanoscience and Technology*, **2014**,	0.6	164
135	Composition-dependent interfacial abruptness in Au-catalyzed Si(1-x)Ge(x)/Si/Si(1-x)Ge(x) nanowire heterostructures. *Nano Letters*, **2014**, 14, 5140-7	11.5	31
134	The initial stage of growth of self-induced GaN nanowires. *Technical Physics Letters*, **2014**, 40, 471-474	0.7	4
133	P□lya distribution and its asymptotics in nucleation theory. *Technical Physics Letters*, **2014**, 40, 177-180	0.7	4
132	Simulation of growth and shape of nanowires in the absence of a catalyst. *Technical Physics Letters*, **2014**, 40, 389-392	0.7	4

131	Record pure zincblende phase in GaAs nanowires down to 5 nm in radius. *Nano Letters*, **2014**, 14, 3938-44	11.5	72
130	Diffusion-induced growth of nanowires: Generalized boundary conditions and self-consistent kinetic equation. *Journal of Crystal Growth*, **2014**, 401, 431-440	1.6	38
129	Size distributions and scaling relations for heterogeneous nucleation and growth of atomic chains. *Journal of Physics: Conference Series*, **2014**, 541, 012089	0.3	2
128	Recipes for crystal phase design in Au-catalyzed III-V nanowires. *Journal of Physics: Conference Series*, **2014**, 541, 012001	0.3	1
127	Size distributions, scaling properties, and Bartelt-Evans singularities in irreversible growth with size-dependent capture coefficients. *Physical Review B*, **2014**, 89,	3.3	16
126	Novel TEM sample preparation using XeF2 selective Etching. *Materials Research Society Symposia Proceedings*, **2014**, 1659, 149-153		
125	Stopping and Resuming at Will the Growth of GaAs Nanowires. *Crystal Growth and Design*, **2013**, 13, 3976-3984	3.5	80
124	Refinement of the Wagner-Ellis formula for the minimum radius and the Givargizov-Chernov formula for the growth rate of nanowire. *Technical Physics Letters*, **2013**, 39, 157-160	0.7	3
123	Modeling GaN nanowire growth on silicon. *Technical Physics Letters*, **2013**, 39, 127-129	0.7	4
122	Ultra-low density InAs quantum dots. *Semiconductors*, **2013**, 47, 1324-1327	0.7	1
121	Modeling InAs quantum-dot formation on the side surface of GaAs nanowires. *Technical Physics Letters*, **2013**, 39, 1047-1052	0.7	4
120	Rate equation approach to understanding the ion-catalyzed formation of peptides. *Journal of Chemical Physics*, **2013**, 138, 244906	3.9	8
119	Unconventional growth mechanism for monolithic integration of III-V on silicon. *ACS Nano*, **2013**, 7, 100-7	16.7	44
118	Readsorption Assisted Growth of InAs/InSb Heterostructured Nanowire Arrays. *Crystal Growth and Design*, **2013**, 13, 878-882	3.5	32
117	Cobalt epitaxial nanoparticles on CaF2/Si(111): Growth process, morphology, crystal structure, and magnetic properties. *Physical Review B*, **2013**, 87,	3.3	10
116	Self-regulated pulsed nucleation in catalyzed nanowire growth. *Physical Review B*, **2013**, 87,	3.3	59
115	Lateral growth and shape of semiconductor nanowires. *Semiconductors*, **2013**, 47, 50-57	0.7	14
114	Elastic energy relaxation and critical thickness for plastic deformation in the core-shell InGaAs/GaAs nanopillars. *Journal of Applied Physics*, **2013**, 113, 104311	2.5	20

113	Tungstate sharpening: a versatile method for extending the profile of ultra sharp tungsten probes. *Review of Scientific Instruments*, **2013**, 84, 035107	1.7	5
112	The nucleation site selection of vapour-liquid-solid nanowires. *Journal of Physics Condensed Matter*, **2013**, 25, 215302	1.8	1
111	Formation of (Ga,Mn)As nanowires and study of their magnetic properties. *Semiconductors*, **2012**, 46, 179-183	0.7	11
110	Growth of semiconductor nanowires at large diffusion lengths. *Technical Physics Letters*, **2012**, 38, 164-167	0.7	1
109	Wetting regime of semiconductor nanowhisker growth: Stability and shape of catalyst droplet. *Technical Physics Letters*, **2012**, 38, 221-224	0.7	2
108	Surface energy and modes of catalytic growth of semiconductor nanowhiskers. *Technical Physics Letters*, **2012**, 38, 311-315	0.7	17
107	Calculating GaAs semiconductor nanoneedle size distribution. *Technical Physics Letters*, **2012**, 38, 358-360	0.7	1
106	Studying the formation of self-assembled (In,Mn)As quantum dots. *Technical Physics Letters*, **2012**, 38, 460-462	0.7	3
105	Growth modeling of CdTe nanowires. *Nanotechnology*, **2012**, 23, 485607	3.4	13
104	Scaling growth kinetics of self-induced GaN nanowires. *Applied Physics Letters*, **2012**, 100, 153101	3.4	57
103	Quantitative description for the growth rate of self-induced GaN nanowires. *Physical Review B*, **2012**, 85,	3.3	69
102	Scaling thermodynamic model for the self-induced nucleation of GaN nanowires. *Physical Review B*, **2012**, 85,	3.3	48
101	Effect of diffusion from a lateral surface on the rate of GaN nanowire growth. *Semiconductors*, **2012** , 46, 838-841	0.7	11
100	Effects of Be doping on InP nanowire growth mechanisms. *Applied Physics Letters*, **2012**, 101, 263106	3.4	22
99	Boron distribution in the core of Si nanowire grown by chemical vapor deposition. *Journal of Applied Physics*, **2012**, 111, 094909	2.5	43
98	Modeling of InAs-InSb nanowires grown by Au-assisted chemical beam epitaxy. *Nanotechnology*, **2012**, 23, 095602	3.4	33
97	Narrowing the length distribution of Ge nanowires. *Physical Review Letters*, **2012**, 108, 105501	7.4	52
96	Influence of shadow effect on the growth and shape of InAs nanowires. *Journal of Applied Physics*, **2012**, 111, 104317	2.5	40

95	Analytical Study of Elastic Relaxation and Plastic Deformation in Nanostructures on Lattice Mismatched Substrates. *Crystal Growth and Design*, **2011**, 11, 5441-5448	3.5	63
94	New mode of vapor-liquid-solid nanowire growth. *Nano Letters*, **2011**, 11, 1247-53	11.5	125
93	Physical consequences of the equivalence of conditions for the steady-state growth of nanowires and the nucleation on triple phase line. *Technical Physics Letters*, **2011**, 37, 53-57	0.7	13
92	Blurring of island size distribution function in theory of nucleation. *Technical Physics Letters*, **2011**, 37, 282-286	0.7	2
91	Surface energy of monolayer formation during nanowire growth by vapor-liquid-solid mechanism. *Technical Physics Letters*, **2011**, 37, 427-430	0.7	3
90	Numerical analysis of the effect of fluctuations on the growth of nuclei during first-order phase transitions. *Technical Physics Letters*, **2011**, 37, 596-600	0.7	1
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